

RJP4301APP

Nch IGBT for Strobe Flash

REJ03G1709-0300 Rev.3.00 Oct 14, 2009

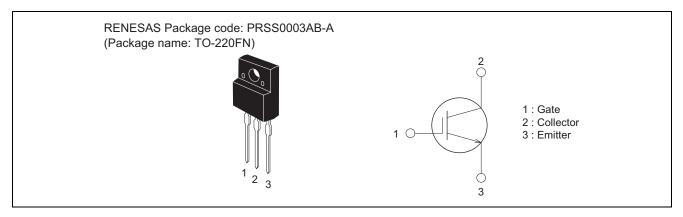
Features

• V_{CES}: 430 V

• TO-220FN package

• High Speed Switching

Outline



Applications

Strobe flash

Maximum Ratings

 $(Tc = 25^{\circ}C)$

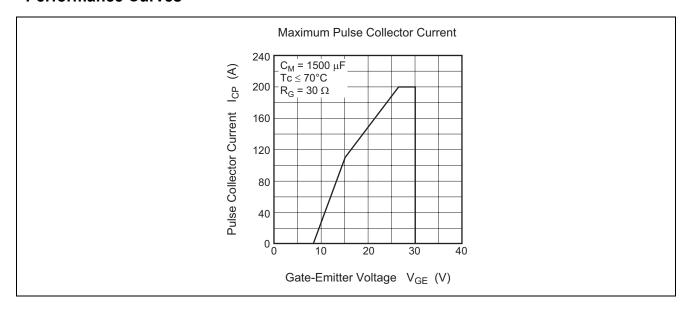
Parameter	Symbol	Ratings	Unit	Conditions
Collector-emitter voltage	V_{CES}	430	V	V _{GE} = 0 V
Gate-emitter voltage	V _{GES}	±33	V	V _{CE} = 0 V, Refer to item 4 under Notes on the Actual Specifications
Collector current (Pulse)	Ісм	200	A	C_M = 1500 μ F (see performance curve)
Maximum power dissipation	Pc	30	W	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	_	2.0	g	Typical value

Electrical Characteristics

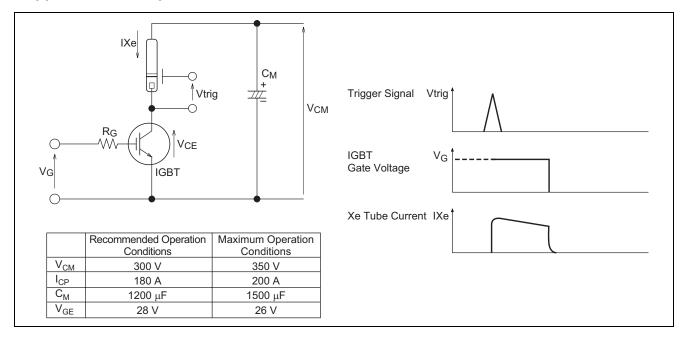
 $(Tj = 25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Collector-emitter breakdown voltage	V _{(BR)CES}	430	_	_	V	$I_C = 100 \mu A, V_{GE} = 0 V$
Collector-emitter leakage current	I _{CES}	_	_	1	μΑ	V _{CE} = 430 V, V _{GE} = 0 V
Gate-emitter leakage current	I _{GES}	_	_	±0.1	μΑ	$V_{GE} = \pm 33 \text{ V}, V_{CE} = 0 \text{ V}$
Gate-emitter threshold voltage	$V_{\text{GE(th)}}$	3.0	_	5.5	V	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$
Collector-emitter saturation voltage	V _{CE(sat)}	_	4.0	10	V	I _C = 200 A, V _{GE} = 26 V
Input capacitance	Cies	_	1150	_	pF	V _{CE} = 25 V
Output capacitance	Coes	_	125	_	pF	V _{GS} = 0
Reverse transfer capacitance	Cres	_	14	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	0.01	_	μS	I _D = 200 A
Rise time	tr	_	0.06	_	μS	V _{GS} = 26 V
Turn-off delay time	$t_{d(off)}$	_	0.15	_	μS	V _{CC} = 300 V
Fall time	t _f	_	0.2	_	μS	$R_G = 25 \Omega$

Performance Curves



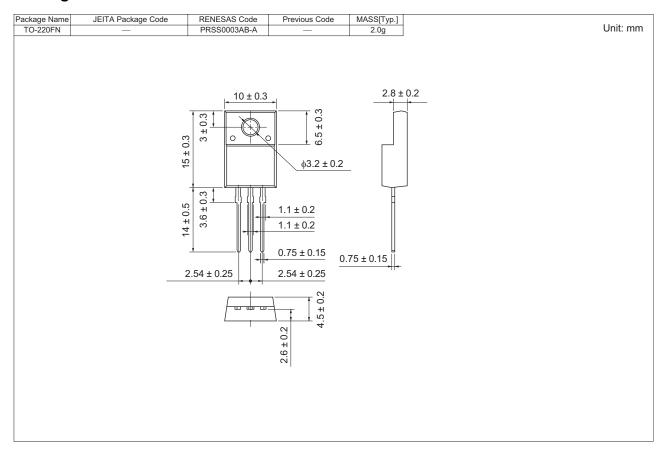
Application Example



Precautions on Usage

- 1. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And peak reverse gate current during turn-off must become less than 1 A. (In general, when $R_{G(off)} = 30 \Omega$, it is satisfied.)
- 2. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully to protect the device from electrostatic charge.
- 3. The operation life should be endured until repeated discharge of 5,000 times under the charge current ($I_{Xe} \le 200~A$: full luminescence condition) of main capacitor. Repetition period under full luminescence condition is over 3 seconds
- 4. Total operation hours applied to the gate-emitter voltage must be within 5,000 hours.

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJP4301APP-00-T2	50 pcs	Magazine (Tube)

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

 1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect of the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

 3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any plan protein. Before purchasing or using any Renesas products listed in this document, in the development is satisfied. The procedure is a such as that disclosed through our website, (http://www.renesas.com)

 3. Renesas has a used reasonable care in compling the information included in this document, but requires a subject to the procedure of the procedure of the procedure of t



RENESAS SALES OFFICES

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510